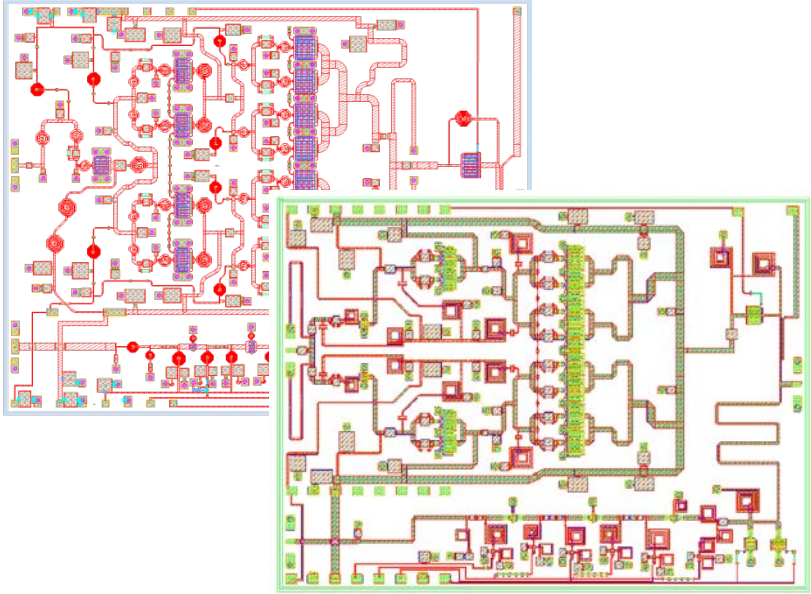


Title:	<i>SINGLE GAN CHIP HPA/LNA FOR RADAR APPLICATIONS</i>		
Contract type	<i>TRP</i>	Budget (K€)	275.000,00
Company (-ies) (including country)	Microwave Engineering Center for Space Applications (MECSA) – ITALY		
Team <i>(name of the participant in the project)</i>	MECSA (prime) Thales Alenia Space Italy Selex Electronic Systems United Monolithic Semiconductors		
(*) Speaker (s)	Ernesto Limiti	Email	limiti@ing.uniroma2.it
Short Speaker Information <i>(experience and involvement in this project)</i>	The presentation will be given by Prof. Ernesto Limiti, coordinator of the project. He is full professor of Electronics at the University of Roma Tor Vergata, EE department. His main research interests include active device characterisation and modelling, circuit design methodologies and advanced semiconductors for future microwave and millimeterwave electronics		
Summary of the activity <i>(maximum 400 words)</i>	<p>Target of the activity is the design of a single-chip integrating integrating low noise amplification (LNA), high power amplification (HPA) and switching (SPDT) functionalities in Gallium Nitride technology.</p> <p>The distinctive feature of the project has been the development of the requested single chip making use of two different European GaN technologies, and namely the UMS GH25 and Selex ES 0.5um technologies. The achieved performance will be presented.</p> 		

(*) The speaker needs to do the registration through the [website](#)